74LVC2G241

Dual buffer/line driver; 3-state

Rev. 09 — 10 June 2008 Product data sheet

1. General description

The 74LVC2G241 is a dual non-inverting buffer/line driver with 3-state outputs. The 3-state outputs are controlled by the output enable inputs $1\overline{OE}$ and 2OE:

- A HIGH level at pin $1\overline{OE}$ causes output 1Y to assume a high-impedance OFF-state.
- A LOW level at pin 2OE causes output 2Y to assume a high-impedance OFF-state.

Schmitt trigger action at all inputs makes the circuit highly tolerant of slower input rise and fall times.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of the 74LVC2G241 as a translator in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

2. Features

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant input/output for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
  - JESD8-7 (1.65 V to 1.95 V)
  - JESD8-5 (2.3 V to 2.7 V)
  - JESD8-B/JESD36 (2.7 V to 3.6 V)
- ESD protection:
  - HBM JESD22-A114E exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
- ±24 mA output drive (V_{CC} = 3.0 V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- Multiple package options
- Specified from –40 °C to +85 °C and –40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVC2G241DP	–40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74LVC2G241DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74LVC2G241GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm	SOT833-1
74LVC2G241GD	–40 °C to +125 °C	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body 3 × 2 × 0.5 mm	SOT996-2
74LVC2G241GM	–40 °C to +125 °C	XQFN8U	plastic extremely thin quad flat package; no leads; 8 terminals; UTLP based; body 1.6 × 1.6 × 0.5 mm	SOT902-1

4. Marking

Table 2. Marking codes

Type number	Marking code
74LVC2G241DP	V241
74LVC2G241DC	V41
74LVC2G241GT	V41
74LVC2G241GD	V41
74LVC2G241GM	V41

5. Functional diagram

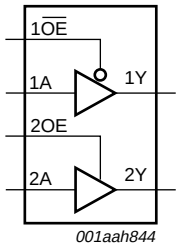


Fig 1. Logic symbol

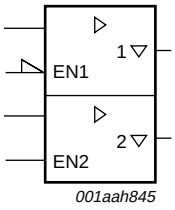


Fig 2. IEC logic symbol

6. Pinning information

6.1 Pinning

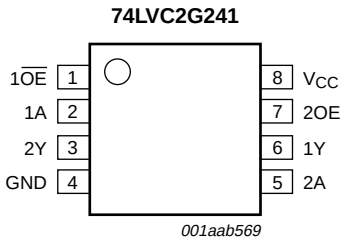


Fig 3. Pin configuration SOT505-2 (TSSOP8) and SOT765-1 (VSSOP8)

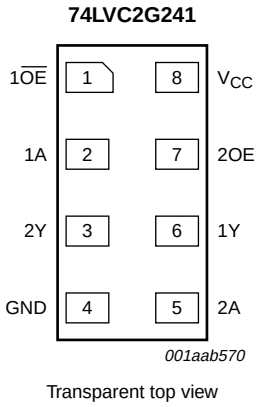


Fig 4. Pin configuration SOT833-1 (XSON8)

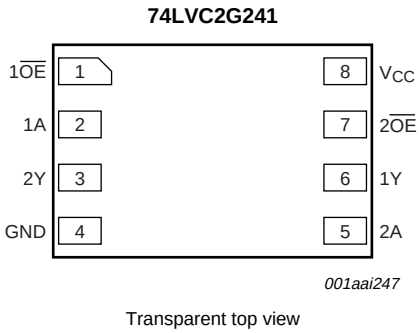


Fig 5. Pin configuration SOT996-2 (XSON8U)

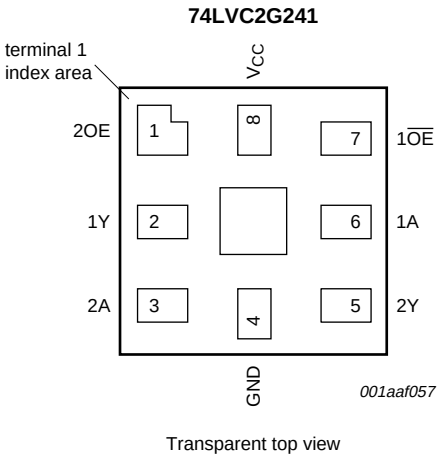


Fig 6. Pin configuration SOT902-1 (XQFN8U)

6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT505-2, SOT765-1, SOT833-1 and SOT996-2	SOT902-1	
$1\overline{OE}$	1	7	output enable input (active LOW)
1A, 2A	2, 5	6, 3	data input
GND	4	4	ground (0 V)

Table 3. Pin description *...continued*

Symbol	Pin		Description
	SOT505-2, SOT765-1, SOT833-1 and SOT996-2	SOT902-1	
1Y, 2Y	6, 3	2, 5	data output
2OE	7	1	output enable input (active HIGH)
V_{CC}	8	8	supply voltage

7. Functional description

Table 4. Function table[1]

Input				Output	
$1\overline{OE}$	1A	2OE	2A	1Y	2Y
L	L	H	L	L	L
L	H	H	H	H	H
H	X	L	X	Z	Z

[1] H = HIGH voltage level;
L = LOW voltage level;
X = don't care;
Z = high-impedance OFF-state.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+6.5	V
I_{IK}	input clamping current	$V_I < 0$ V		–50	-	mA
V_I	input voltage		[1]	–0.5	+6.5	V
I_{OK}	output clamping current	$V_O > V_{CC}$ or $V_O < 0$ V		-	±50	mA
V_O	output voltage	enable mode	[1]	–0.5	V_{CC} + 0.5	V
		disable mode	[1]	–0.5	+6.5	V
		Power-down mode	[1][2]	–0.5	+6.5	V
I_O	output current	V_O = 0 V to V_{CC}		-	±50	mA
I_{CC}	supply current			-	100	mA
I_{GND}	ground current			–100	-	mA
T_{stg}	storage temperature			–65	+150	°C
P_{tot}	total power dissipation	T_{amb} = –40 °C to +125 °C	[3]	-	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When V_{CC} = 0 V (Power-down mode), the output voltage can be 5.5 V in normal operation.

[3] For TSSOP8 packages: above 55 °C the value of P_{tot} derates linearly at 2.5 mW/K.
For VSSOP8 packages: above 110 °C the value of P_{tot} derates linearly at 8.0 mW/K.
For XSON8, XSON8U and XQFN8U packages: above 45 °C the value of P_{tot} derates linearly at 2.4 mW/K.

9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		1.65	5.5	V
V_I	input voltage		0	5.5	V
V_O	output voltage	V_{CC} = 1.65 V to 5.5 V; enable mode	0	V_{CC}	V
		V_{CC} = 1.65 V to 5.5 V; disable mode	0	5.5	V
		V_{CC} = 0 V; Power-down mode	0	5.5	V
T_{amb}	ambient temperature		–40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 1.65 V to 2.7 V	-	20	ns/V
		V_{CC} = 2.7 V to 5.5 V	-	10	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
T_{amb} = –40 °C to +85 °C						
V_{IH}	HIGH-level input voltage	V_{CC} = 1.65 V to 1.95 V	0.65 × V_{CC}	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		V_{CC} = 2.7 V to 3.6 V	2.0	-	-	V
		V_{CC} = 4.5 V to 5.5 V	0.7 × V_{CC}	-	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 1.65 V to 1.95 V	-	-	0.35 × V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V_{CC} = 2.7 V to 3.6 V	-	-	0.8	V
		V_{CC} = 4.5 V to 5.5 V	-	-	0.3 × V_{CC}	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}				
		I_O = 100 µA; V_{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		I_O = 4 mA; V_{CC} = 1.65 V	-	-	0.45	V
		I_O = 8 mA; V_{CC} = 2.3 V	-	-	0.3	V
		I_O = 12 mA; V_{CC} = 2.7 V	-	-	0.4	V
		I_O = 24 mA; V_{CC} = 3.0 V	-	-	0.55	V
		I_O = 32 mA; V_{CC} = 4.5 V	-	-	0.55	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}				
		I_O = –100 µA; V_{CC} = 1.65 V to 5.5 V	V_{CC} – 0.1	-	-	V
		I_O = –4 mA; V_{CC} = 1.65 V	1.2	-	-	V
		I_O = –8 mA; V_{CC} = 2.3 V	1.9	-	-	V
		I_O = –12 mA; V_{CC} = 2.7 V	2.2	-	-	V
		I_O = –24 mA; V_{CC} = 3.0 V	2.3	-	-	V
		I_O = –32 mA; V_{CC} = 4.5 V	3.8	-	-	V
I_I	input leakage current	V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	±0.1	±5	µA

Table 7. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL}; V_O = 5.5 V or GND; V_{CC} = 3.6 V	-	±0.1	±10	µA
I_{OFF}	power-off leakage current	V_I or V_O = 5.5 V; V_{CC} = 0 V	-	±0.1	±10	µA
I_{CC}	supply current	V_I = 5.5 V or GND; I_O = 0 A; V_{CC} = 1.65 V to 5.5 V	-	0.1	10	µA
ΔI_{CC}	additional supply current	per pin; $V_I = V_{CC} - 0.6$ V; I_O = 0 A; V_{CC} = 2.3 V to 5.5 V	-	5	500	µA
C_I	input capacitance		-	2	-	pF
T_{amb} = −40 °C to +125 °C						
V_{IH}	HIGH-level input voltage	V_{CC} = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		V_{CC} = 2.7 V to 3.6 V	2.0	-	-	V
		V_{CC} = 4.5 V to 5.5 V	$0.7 \times V_{CC}$	-	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V_{CC} = 2.7 V to 3.6 V	-	-	0.8	V
		V_{CC} = 4.5 V to 5.5 V	-	-	$0.3 \times V_{CC}$	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_O = 100 µA; V_{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		I_O = 4 mA; V_{CC} = 1.65 V	-	-	0.70	V
		I_O = 8 mA; V_{CC} = 2.3 V	-	-	0.45	V
		I_O = 12 mA; V_{CC} = 2.7 V	-	-	0.60	V
		I_O = 24 mA; V_{CC} = 3.0 V	-	-	0.80	V
		I_O = 32 mA; V_{CC} = 4.5 V	-	-	0.80	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_O = −100 µA; V_{CC} = 1.65 V to 5.5 V	$V_{CC} - 0.1$	-	-	V
		I_O = −4 mA; V_{CC} = 1.65 V	0.95	-	-	V
		I_O = −8 mA; V_{CC} = 2.3 V	1.7	-	-	V
		I_O = −12 mA; V_{CC} = 2.7 V	1.9	-	-	V
		I_O = −24 mA; V_{CC} = 3.0 V	2.0	-	-	V
		I_O = −32 mA; V_{CC} = 4.5 V	3.4	-	-	V
I_I	input leakage current	V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	-	±20	µA
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL}; V_O = 5.5 V or GND; V_{CC} = 3.6 V	-	-	±20	µA
I_{OFF}	power-off leakage current	V_I or V_O = 5.5 V; V_{CC} = 0 V	-	-	±20	µA
I_{CC}	supply current	V_I = 5.5 V or GND; I_O = 0 A; V_{CC} = 1.65 V to 5.5 V	-	-	40	µA
ΔI_{CC}	additional supply current	per pin; $V_I = V_{CC} - 0.6$ V; I_O = 0 A; V_{CC} = 2.3 V to 5.5 V	-	-	5	mA

[1] Typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 10.

Symbol	Parameter	Conditions		−40 °C to +85 °C			−40 °C to +125 °C		Unit
				Min	Typ[1]	Max	Min	Max	
t_{pd}	propagation delay	nA to nY; see Figure 7	[2]						
		V_{CC} = 1.65 V to 1.95 V		1.0	4.5	8.8	1.0	11.0	ns
		V_{CC} = 2.3 V to 2.7 V		0.5	2.8	4.9	0.5	6.3	ns
		V_{CC} = 2.7 V		1.0	2.8	4.7	1.0	5.9	ns
		V_{CC} = 3.0 V to 3.6 V		0.5	2.6	4.3	0.5	5.4	ns
		V_{CC} = 4.5 V to 5.5 V		0.5	2.1	3.7	0.5	4.6	ns
t_{en}	enable time	$1\overline{OE}$ to 1Y; see Figure 8	[3]						
		V_{CC} = 1.65 V to 1.95 V		1.5	5.2	9.9	1.5	12.4	ns
		V_{CC} = 2.3 V to 2.7 V		1.0	3.1	5.6	1.0	7.0	ns
		V_{CC} = 2.7 V		1.5	3.2	5.5	1.5	6.9	ns
		V_{CC} = 3.0 V to 3.6 V		0.5	2.7	4.7	0.5	5.9	ns
		V_{CC} = 4.5 V to 5.5 V		0.5	2.0	3.8	0.5	4.8	ns
		2OE to 2Y; see Figure 9	[3]						
		V_{CC} = 1.65 V to 1.95 V		1.0	4.3	8.8	1.0	11.0	ns
		V_{CC} = 2.3 V to 2.7 V		1.0	2.7	4.7	1.0	5.9	ns
		V_{CC} = 2.7 V		1.0	2.7	4.6	1.0	5.8	ns
		V_{CC} = 3.0 V to 3.6 V		1.0	2.5	4.1	1.0	5.1	ns
		V_{CC} = 4.5 V to 5.5 V		0.5	1.9	3.3	0.5	4.1	ns
t_{dis}	disable time	$1\overline{OE}$ to 1Y; see Figure 8	[4]						
		V_{CC} = 1.65 V to 1.95 V		1.0	3.2	11.6	1.0	14.1	ns
		V_{CC} = 2.3 V to 2.7 V		0.5	2.2	5.8	0.5	7.6	ns
		V_{CC} = 2.7 V		1.0	2.8	4.6	1.0	5.9	ns
		V_{CC} = 3.0 V to 3.6 V		1.0	2.6	4.4	1.0	5.7	ns
		V_{CC} = 4.5 V to 5.5 V		0.5	2.0	3.4	0.5	4.6	ns
		2OE to 2Y; see Figure 9	[4]						
		V_{CC} = 1.65 V to 1.95 V		1.0	3.6	12.5	1.0	15.2	ns
		V_{CC} = 2.3 V to 2.7 V		0.5	2.0	5.2	0.5	6.9	ns
		V_{CC} = 2.7 V		1.5	3.2	4.9	1.5	6.3	ns
		V_{CC} = 3.0 V to 3.6 V		1.0	2.8	4.2	1.0	5.4	ns
		V_{CC} = 4.5 V to 5.5 V		0.5	2.0	3.3	0.5	4.4	ns

Table 8. Dynamic characteristics *…continued*

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 10.

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
C_{PD}	power dissipation capacitance	per buffer; V_I = GND to V_{CC} [5]						
		output enabled	-	20	-	-	-	pF
		output disabled	-	5	-	-	-	pF

[1] Typical values are measured at nominal V_{CC} and at T_{amb} = 25 °C.

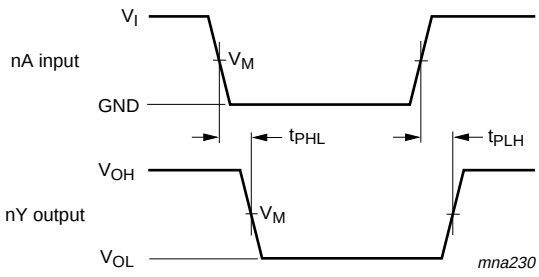
[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

[3] t_{en} is the same as t_{PZH} and t_{PZL}.

[4] t_{dis} is the same as t_{PLZ} and t_{PHZ}.

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in µW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V;
N = number of inputs switching;
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

12. Waveforms



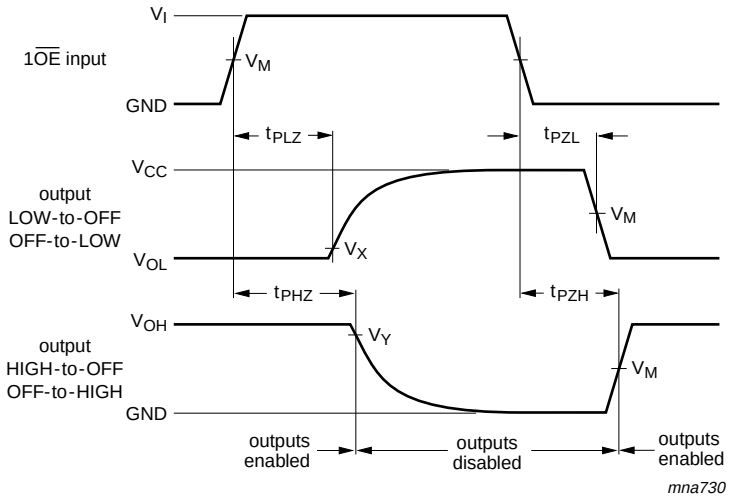
Measurement points are given in Table 9.

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 7. The data input (nA) to output (nY) propagation delays

Table 9. Measurement points

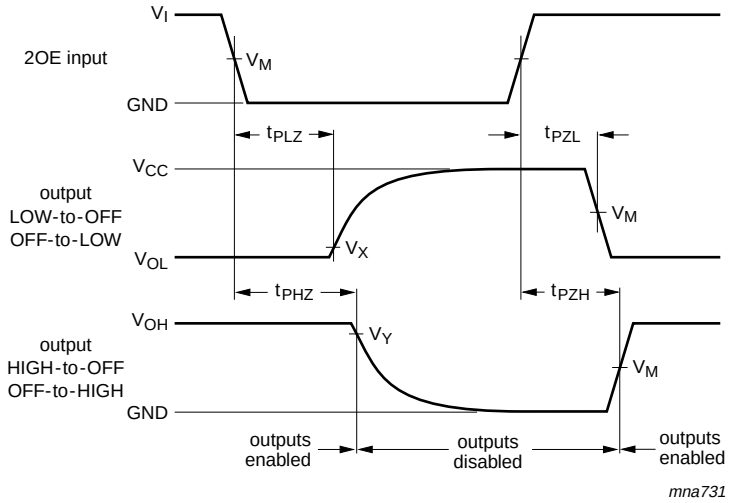
Supply voltage	Input	Output		
V_{CC}	V_M	V_M	V_X	V_Y
1.65 V to 1.95 V	0.5 × V_{CC}	0.5 × V_{CC}	V_{OL} + 0.15 V	V_{OH} – 0.15 V
2.3 V to 2.7 V	0.5 × V_{CC}	0.5 × V_{CC}	V_{OL} + 0.15 V	V_{OH} – 0.15 V
2.7 V	1.5 V	1.5 V	V_{OL} + 0.3 V	V_{OH} – 0.3 V
3.0 V to 3.6 V	1.5 V	1.5 V	V_{OL} + 0.3 V	V_{OH} – 0.3 V
4.5 V to 5.5 V	0.5 × V_{CC}	0.5 × V_{CC}	V_{OL} + 0.3 V	V_{OH} – 0.3 V



Measurement points are given in Table 9.

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

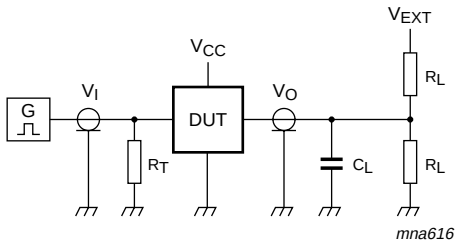
Fig 8. Enable and disable times for input 1$\overline{OE}$



Measurement points are given in Table 9.

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 9. Enable and disable times for input 2OE



Test data is given in Table 10.

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

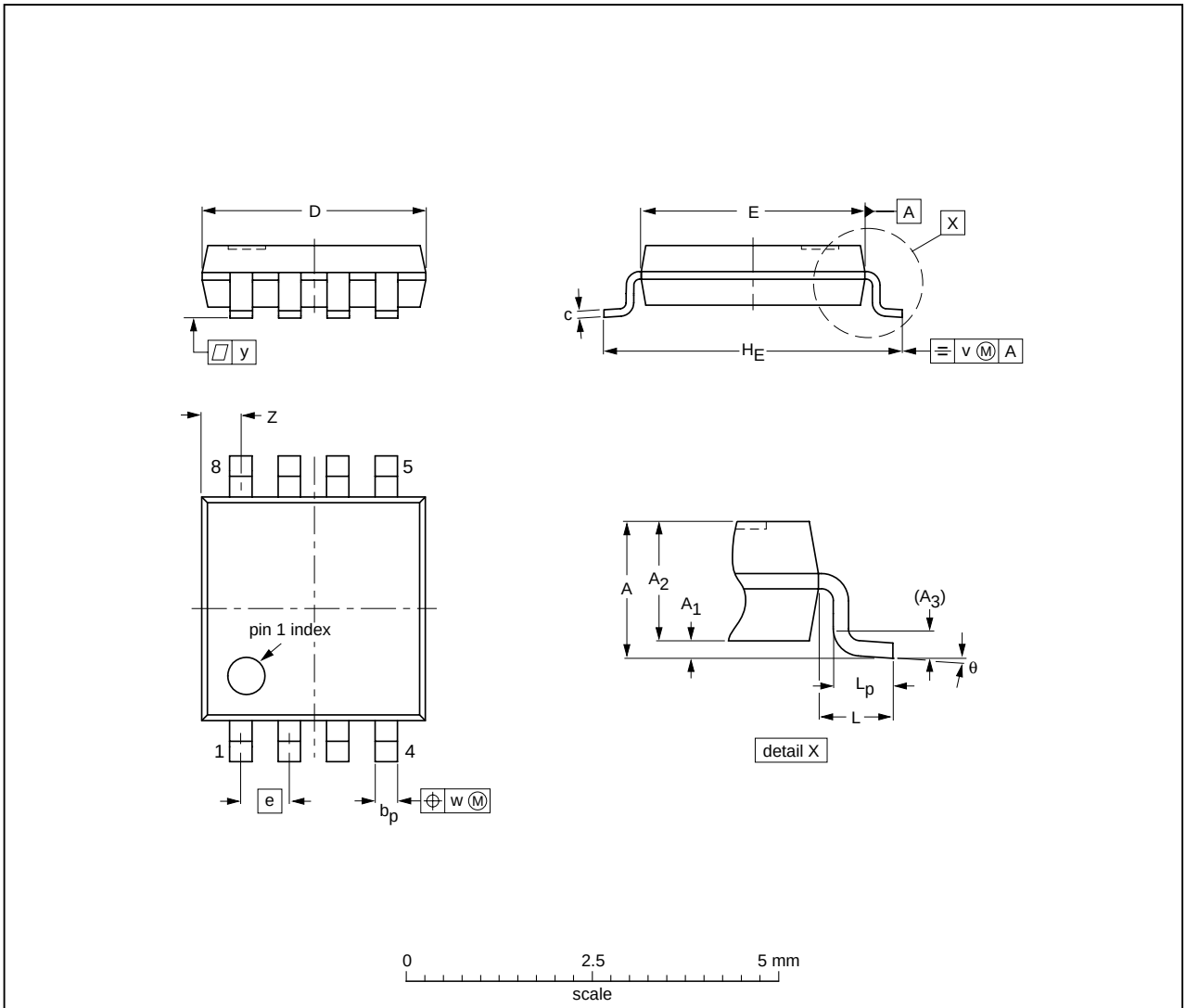
Fig 10. Load circuit for measuring switching times

Table 10. Test data

Supply voltage	Input	Load		V_{EXT}		
	V_I	C_L	R_L	t_{PLH}, t_{PHL}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
1.65 V to 1.95 V	V_{CC}	30 pF	1 kΩ	open	GND	$2 \times V_{CC}$
2.3 V to 2.7 V	V_{CC}	30 pF	500 Ω	open	GND	$2 \times V_{CC}$
2.7 V	2.7 V	50 pF	500 Ω	open	GND	6 V
3.0 V to 3.6 V	2.7 V	50 pF	500 Ω	open	GND	6 V
4.5 V to 5.5 V	V_{CC}	50 pF	500 Ω	open	GND	$2 \times V_{CC}$

13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	v	w	y	$Z^{(1)}$	θ
mm	1.1	0.15 0.00	0.95 0.75	0.25	0.38 0.22	0.18 0.08	3.1 2.9	3.1 2.9	0.65	4.1 3.9	0.5	0.47 0.33	0.2	0.13	0.1	0.70 0.35	8° 0°

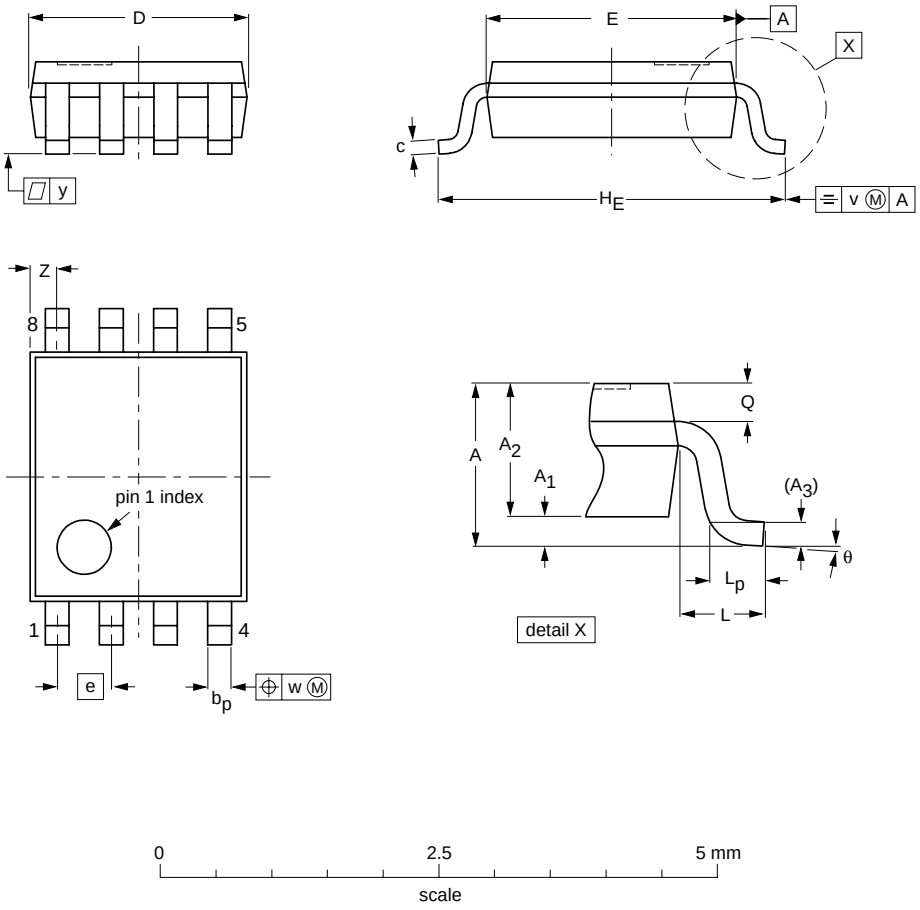
Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT505-2		- - -				02-01-16

Fig 11. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm **SOT765-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(2)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

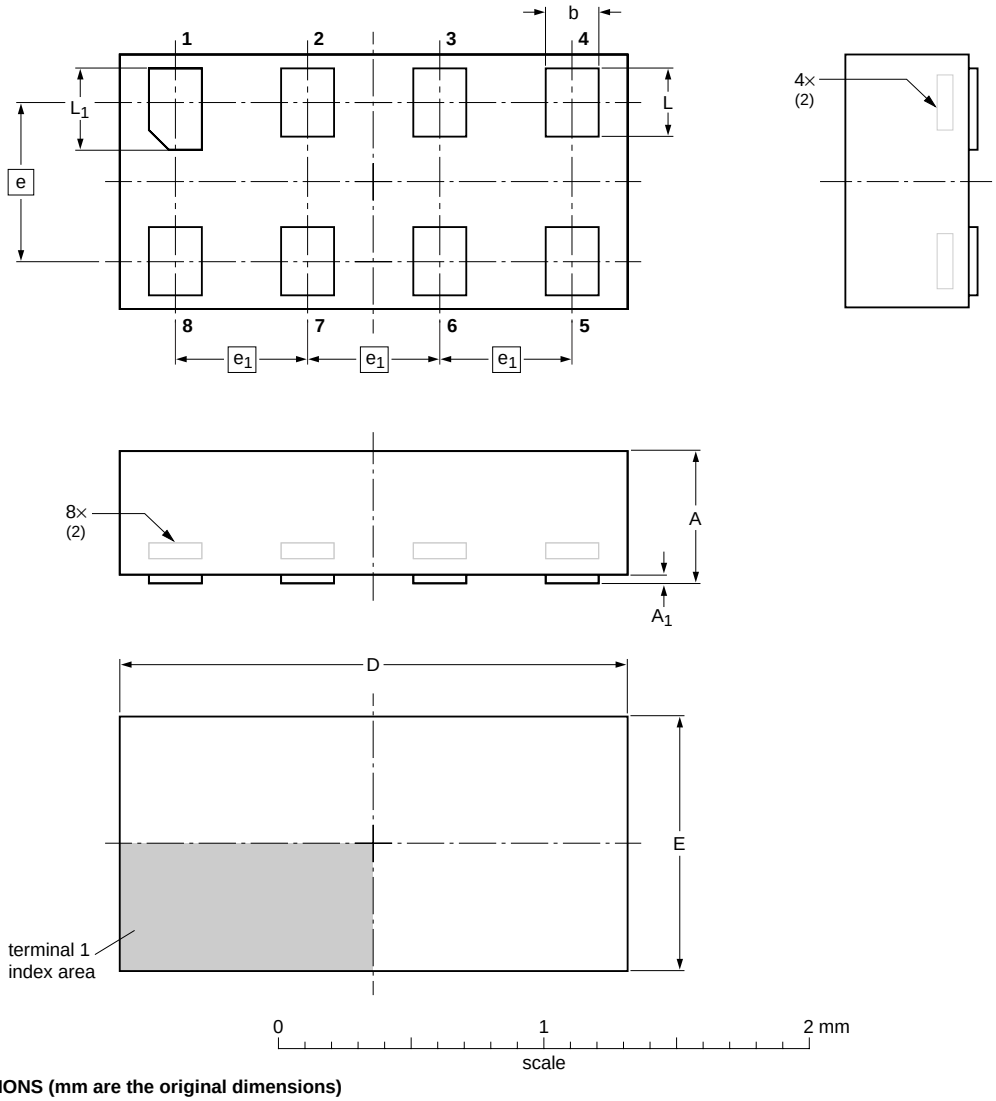
Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT765-1		MO-187				02-06-07

Fig 12. Package outline SOT765-1 (VSSOP8)

XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 1 x 1.95 x 0.5 mm **SOT833-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A(1) max	A1 max	b	D	E	e	e1	L	L1
mm	0.5	0.04	0.25 0.17	2.0 1.9	1.05 0.95	0.6	0.5	0.35 0.27	0.40 0.32

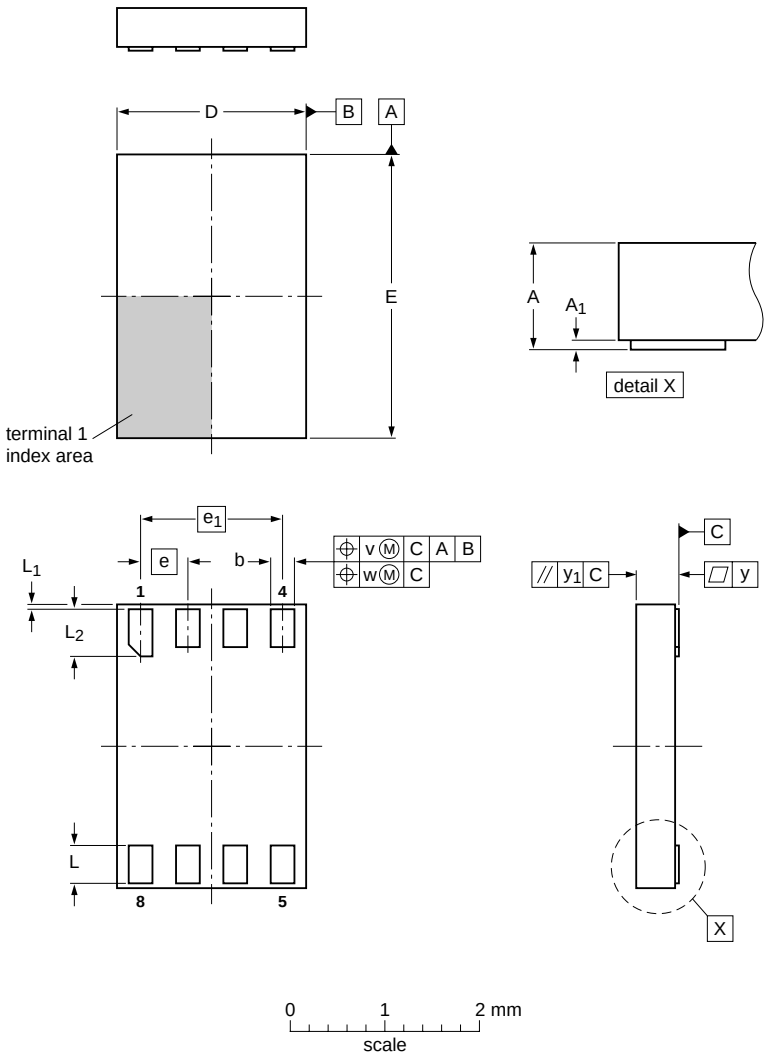
Notes

1. Including plating thickness.
2. Can be visible in some manufacturing processes.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT833-1	- - -	MO-252	- - -			~~07-11-14~~ 07-12-07

Fig 13. Package outline SOT833-1 (XSON8)

XSON8U: plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body 3 x 2 x 0.5 mm **SOT996-2**



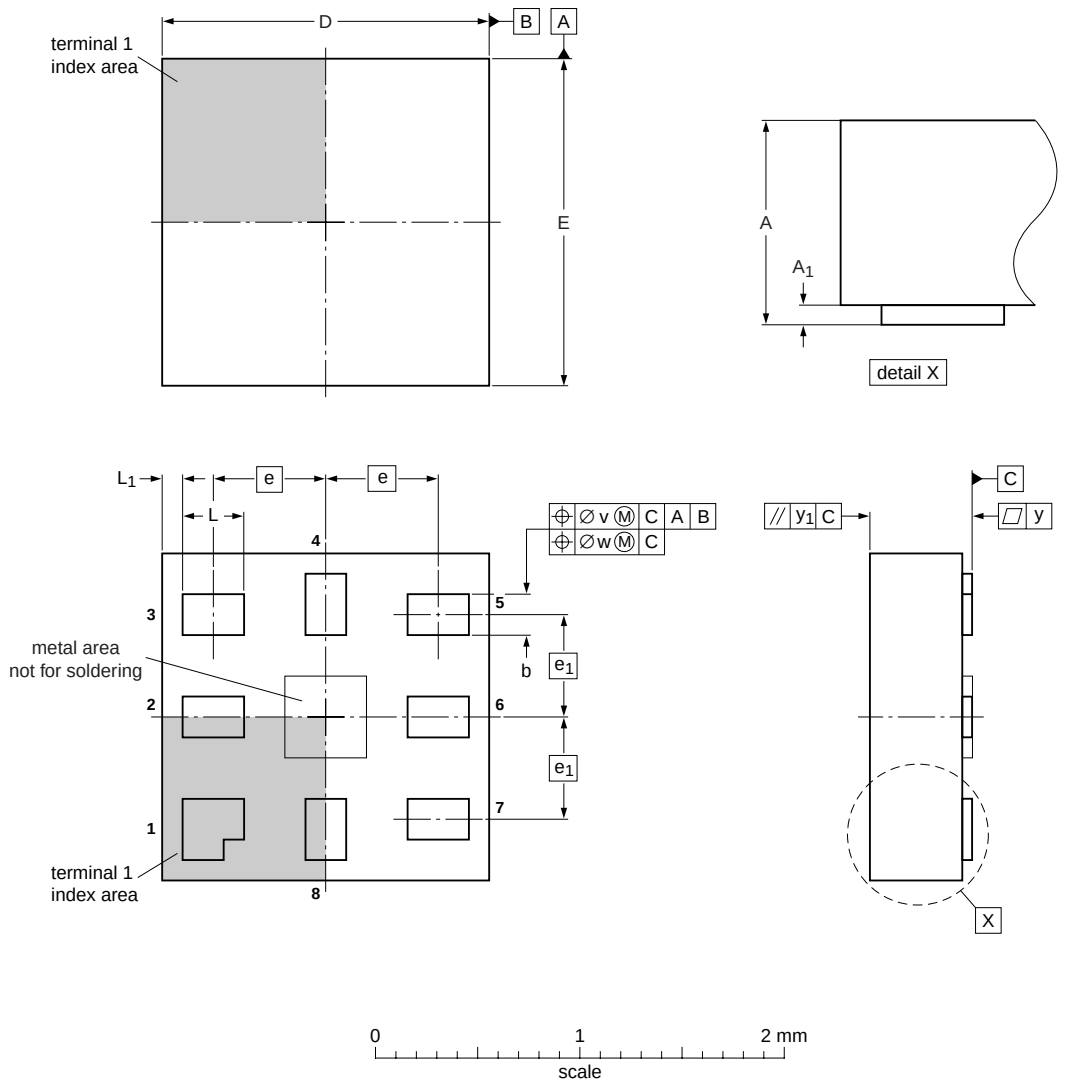
DIMENSIONS (mm are the original dimensions)

UNIT	A max	A_1	b	D	E	e	e_1	L	L_1	L_2	v	w	y	y_1
mm	0.5	0.05 0.00	0.35 0.15	2.1 1.9	3.1 2.9	0.5	1.5	0.5 0.3	0.15 0.05	0.6 0.4	0.1	0.05	0.05	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT996-2	- - -		- - -			~~07-12-18~~ 07-12-21

Fig 14. Package outline SOT996-2 (XSON8U)

XQFN8U: plastic extremely thin quad flat package; no leads; 8 terminals; UTLP based; body 1.6 x 1.6 x 0.5 mm **SOT902-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max	A_1	b	D	E	e	e_1	L	L_1	v	w	y	y_1
mm	0.5	0.05 0.00	0.25 0.15	1.65 1.55	1.65 1.55	0.55	0.5	0.35 0.25	0.15 0.05	0.1	0.05	0.05	0.05

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT902-1	- - -	MO-255	- - -			~~05-11-25~~ 07-11-14

Fig 15. Package outline SOT902-1 (XQFN8U)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC2G241_9	20080610	Product data sheet	-	74LVC2G241_8
Modifications:	• Added type number 74LVC2G241GD (XSON8U package)			
74LVC2G241_8	20080312	Product data sheet	-	74LVC2G241_7
74LVC2G241_7	20071005	Product data sheet	-	74LVC2G241_6
74LVC2G241_6	20060922	Product data sheet	-	74LVC2G241_5
74LVC2G241_5	20050202	Product specification	-	74LVC2G241_4
74LVC2G241_4	20040922	Product specification	-	74LVC2G241_3
74LVC2G241_3	20030311	Product specification	-	74LVC2G241_2
74LVC2G241_2	20030129	Product specification	-	74LVC2G241_1
74LVC2G241_1	20021030	Product specification	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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18. Contents

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